

Microscopic-scale Defect Analysis on Ga₂O₃ through Microscopy

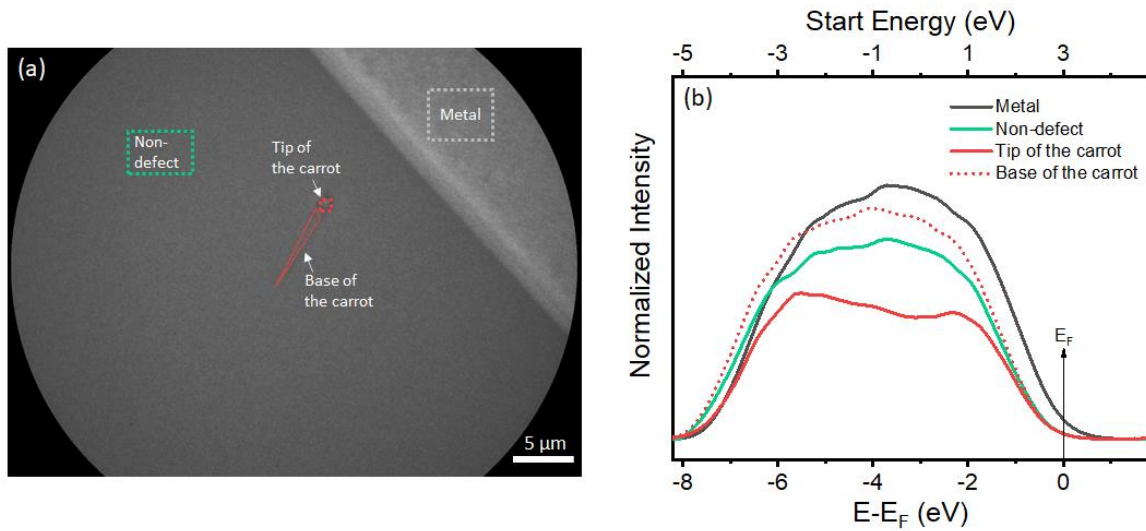


Fig. 1. (a) PEEM image of the carrot defect in Ga₂O₃ epi-layer grown with HVPE. The field of view is 50 μm. (b) Normalized photoelectron spectroscopy illuminated by 193 nm light on metal, non-defect and carrot defect.

References

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